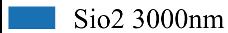
6inch 500nm c-cut SiCOI SPEC



Transfer SIC Layer

No.	Item	Specification	Remark
1	Poly type	4H	
2	Type	HPSI	
3	Resistivity	≥1E8ohm.cm	
4	Orientation	<0001>	
5	off Orientation	0±0.25°	
6	SiC Thickness (21 Pts)	500±100nm	Edge exclusion 12mm
7	Frontside finish	C -face CMP	
8	Frontside Rms-C	≤0.5nm（5μm*5μm）	Edge exclusion 5mm
Modified Layer			
1	Material	Al2O3	
2	Thickness	1-20 nm	Process Guarantee
Oxide Layer			
1	Oxide thickness	3000±5% nm	Edge exclusion 5mm

Handle SI Substrate

No.	Item	Specification	Remark
1	Growth Method	CZ	
2	Orientation	<100>	
3	Resistivity	1−100ohm.cm	
4	Dopant	P/B	
5	Si Thickness	675±25um	
6	Primary flat	<110>±1.0	
7	Primary flat length	47.5±2 mm	
Overall Wafer Characteristics			
1	Diameter	150 ±0.2 mm	
2	TTV	≤5μm	Edge exclusion 5mm
3	Bow	± 50 μm	Edge exclusion 5mm
4	Warp	≤50μm	Edge exclusion 5mm
5	Thickness	676±25μm	Edge exclusion 5mm
6	Scratches（visual inspection）	None	
7	Crack（visual inspection）	None	
Visual Defect of Backside			
1	Laser Mark	Backside	
2	Backside finish	Etched with Oxide	

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